

T-01-15

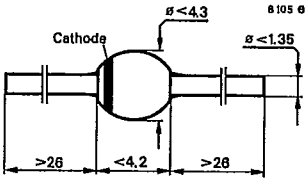
**Silicon Mesa Diodes**

**Application:** High voltage rectifier

**Features:**

- Glass passivated junction
- Hermetically sealed package

**Dimensions in mm**



Sintered glass case  
SOD 64  
Weight max. 1.0 g

**Marking:** By letters

**Absolute maximum ratings**

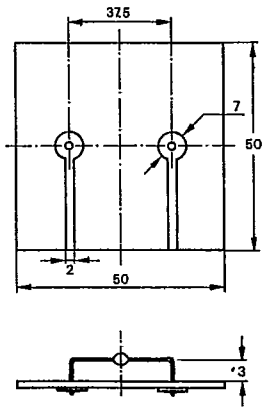
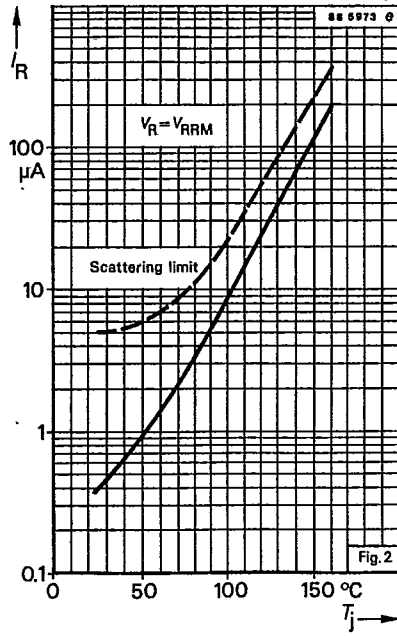
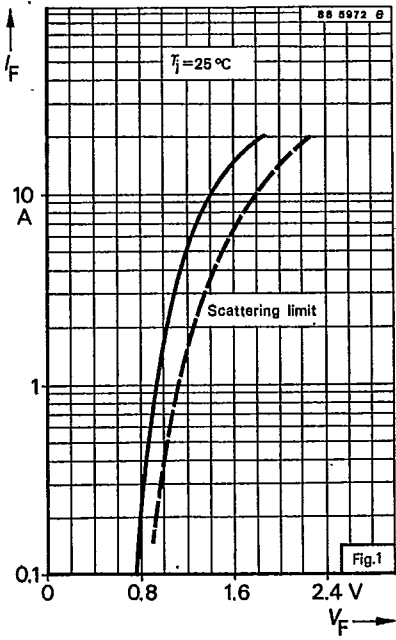
		BY 228/13	BY 228/15	
Surge reverse voltage	$V_{RSM}$	1300	1500	V
Reverse voltage	$V_R$	1000	1200	V
Surge forward current				
$t_p = 10 \text{ ms}$	$I_{FSM}$	50		A
Average forward current	$I_{FAV}$	3		A
Junction temperature	$T_j$	140		°C
Storage temperature range	$T_{stg}$	-65...+175		°C

**Maximum thermal resistance**

Junction ambient on PC board with spacing 37.5 mm	$R_{thJA}$	70		K/W
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**Characteristics**

		Min.	Typ.	Max.	
$T_j = 25 \text{ °C}$ , unless otherwise specified					
Forward voltage					
$I_F = 5 \text{ A}$	$V_F$			1.5	V
Reverse current					
$V_R = 1000 \text{ V}$	BY 228/13 $I_R$	2		5	μA
$V_R = 1200 \text{ V}$	BY 228/15 $I_R$	2		5	μA
$T_j = 140 \text{ °C}$ , $V_R = 1000 \text{ V}$	BY 228/13 $I_R$			140	μA
$V_R = 1200 \text{ V}$	BY 228/15 $I_R$			140	μA
Total reverse recovery time					
$I_F = 1 \text{ A}$ , $\frac{-d_i}{d_t} = 0.05 \text{ A/}\mu\text{s}$	$t_{rr}$			20	μs



Epoxy glass hard tissue, board thickness: 1.5 mm  
 $R_{thJA} \leq 70 \text{ K/W}$

Fig.3

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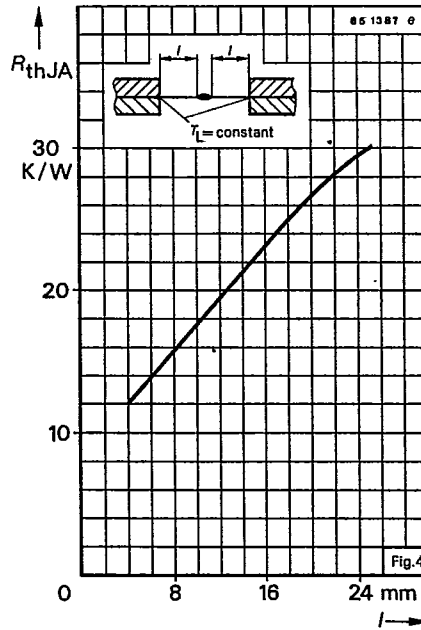


Fig.4